


- L1: (574) bit and first near magnetic adj layer
- L2: (538) 1 and second near magnetic adj layer
- L3: (4796) "3" and (non?magnetic non-magnetic no
- L4: (276) 2 and (non?magnetic non-magnetic nonr
- L7: (76) 4 and 365/\$.ccls.
- L8: (23) 4 and 438/\$.ccls.
- L9: (22) 4 and 257/\$.ccls.
- L10: (1328) (365/158,171,173).CCLS.
- L11: (487) (438/48).CCLS.
- L12: (1866) (257/295,421-427).CCLS.
- L13: (1) 7 and 12
- L14: (0) 7 and 11
- L15: (61) 7 and 10

 Favorites

Query	<input type="button" value="Browse"/> <input type="button" value="Query"/> <input type="button" value="Clear"/>
DBs	USPAT; US-POPUS; EPD; JPD; DERWENT; ISM; TDB
Default operator:	OR
	<input checked="" type="checkbox"/> Plurals <input checked="" type="checkbox"/> Highlight all hit terms initially
7 and 10	

	U	1	Document ID	Issue Date	Pages	Title	Current	Cur Re	Inventor	S	C	P	2	3
1			US 20030133323 A1	20030717	8	Magnetoresistive memor	365/158		Nejad, Hasan					
2			US 20030112655 A1	20030619	26	Magnetic memory device	365/158	365/	Hosotani, Keiji					
3			US 20030090932 A1	20030515	18	ASYMMETRIC MRAM	365/158		Deak, James G.					
4			US 20030067800 A1	20030410	21	Magnetoresistive element	365/158		Koganei, Akio					
5			US 20030063491 A1	20030403	11	Magneto resistive film, m	365/158	365/	Ikeda, Takashi					
6			US 20030048658 A1	20030313	8	Magnetic element with a	365/158		Chen, Eugene Youj					
7			US 20030002330 A1	20030102	18	Magnetoresistive element	365/158		Nishimura, Naoki					
8			US 20020196657 A1	20021226	24	Magnetic memory device	365/158		Kato, Yuukoh					
9			US 20020191437 A1	20021219	18	Magnetic memory device	365/158	365/	Yamada, Kouichi					